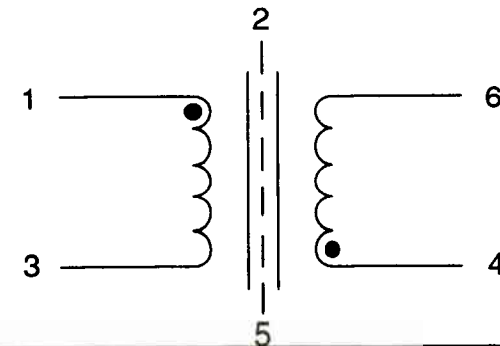
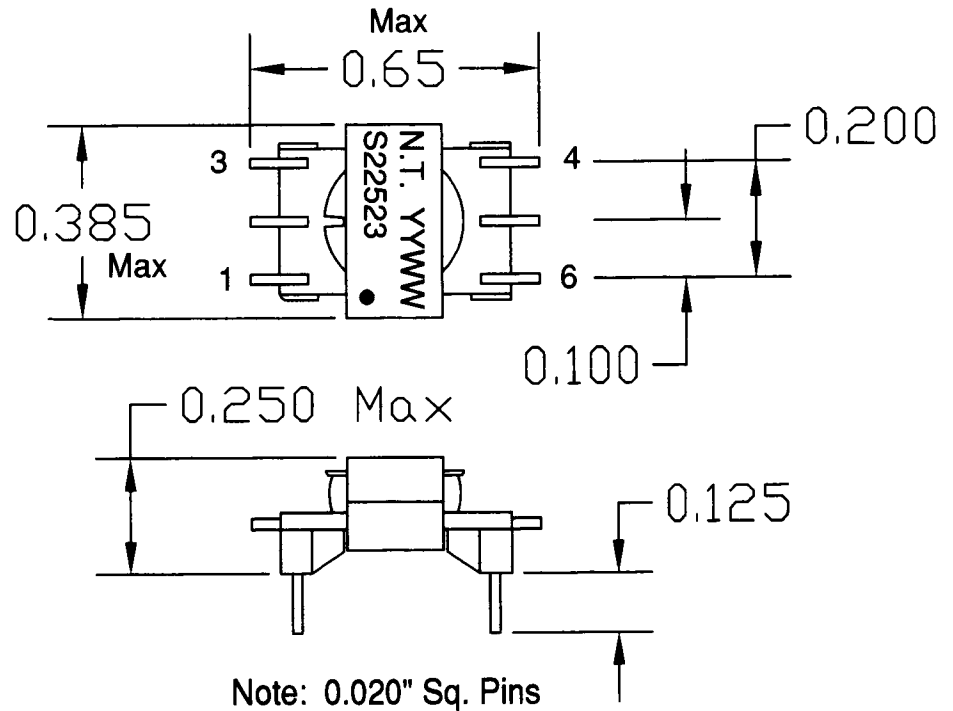


SPECIFICATIONS:

1. INDUCTANCE: @ 10 kHz, 0.1 Vrms,
1 - 3 > 225 uHy
2. DCR: mOHMS Nom
1 - 3 = 0.1
4 - 6 = 0.1
3. LEAKAGE INDUCTANCE: 1 - 3, 1.0 V @ 100kHz
SHORT 4 - 6 < 0.7 uHy
4. INTERWINDING CAPACITANCE: with Shield
Grounded
1 - 3 to 4 - 6 @ 100 KHz, 1.0V < 2.0 pf
5. TURNS AND PHASE:
1 - 3 : 4 - 6 = 1 : 1.22 +/- 2%
- 6 DIELECTRIC STRENGTH:
1500 VAC 1 sec

Note: Designed to operate with Crystal Semiconductor
CS8401.8402, 8411 & 8412



REV.	DATE	ECN	BY	DESCRIPTION	
TOLERANCES ON				Newava Tech. Watertown, SD 57201 605-886-0264	Transformer Power, 1:1.22
.XXX ± -	.XX ± -	ANGLE ± -	DATE		
DRAWN:			SCALE	MODEL	DRAWING NO.
CHECKED: -					S22523
APPROVED: -				NEXT ASSY:	A
THIS PRINT MUST NOT BE COPIED IN WHOLE OR IN PART OR USED DETRIMENTALLY TO OUR INTEREST					SHEET 1 OF 1